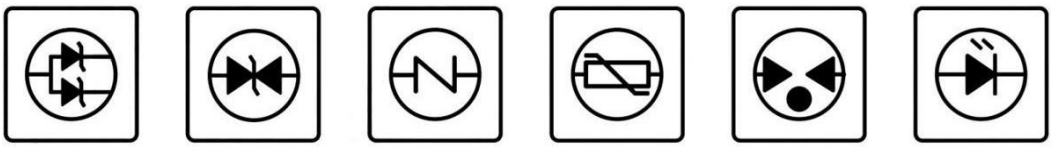
MSKSEMI 美森科
SEMICONDUCTOR



GBU25005-MS THRU GBU2510-MS

Product specification

GBU25005-MS THRU GBU2510-MS

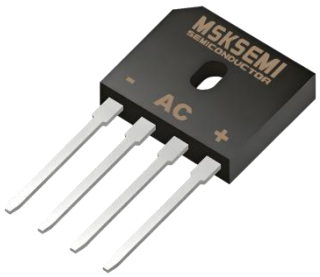
VOLTAGE RANGE: 50 - 1000V
CURRENT: 25 A

FEATURES

- Surge overload rating -350 amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Plastic material has U/L lammability classification 94V-0

REFERENCE NEWS

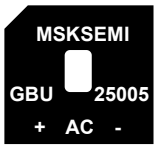
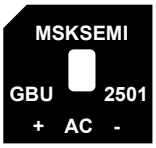
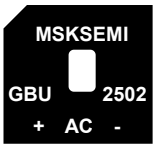
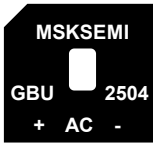
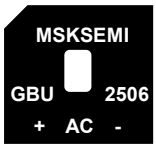
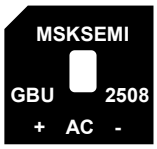
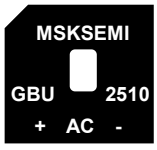
GBU



MECHANICAL DATA

- **Case** : JEDEC GBU Molded plastic body
- **Terminals** : Solder plated, solderable per MIL-STD-750,Method 2026
- **Polarity** : Polarity symbol marking on body
- **Mounting Position**: Any

Marking

GBU25005-MS	GBU2501-MS	GBU2502-MS	GBU2504-MS
			
GBU2506-MS	**GBU2508-MS**	**GBU2510-MS**	
			

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwisespecified.
Single phase half-wave 60Hz,resistive or inductive load,for capacitive load current derate by 20%.

Parameter	SYMBOLS	GBU25005 -MS	GBU2501 -MS	GBU2502 -MS	GBU2504 -MS	GBU2506 -MS	GBU2508 -MS	GBU2510 -MS	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward(with heatsink NOTE 2) Rectified current @T_C =100°C(without heatsink)	$I_{(AV)}$	25.0 4.2							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	300							A
Rating for Fusing(t<8.3ms)	I^2t	508							A^2s
Maximum forward voltage at 12.5A DC	V_F	1.0							V
Maximum DC reverse current at T_A=25°C rated DC blocking voltage T_A=125°C	I_R	5							μA
		0.5							mA
Typical Junction Capacitance (Note 1)	C_J	70							pF
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$	2.2							°C/W
Operating junction temperature range	T_J	-55 to +150							°C
storage temperature range	T_{STG}	-55 to +150							°C

NOTES:

1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2.Device mounted on 100mm*100mm*1.6mm cu plate heatsink.

3.The typical data above is for reference only.

RATINGAND CHARACTERISTIC CURVES (GBU25005-MS THRU GBU2510-MS)

FIG.1-DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

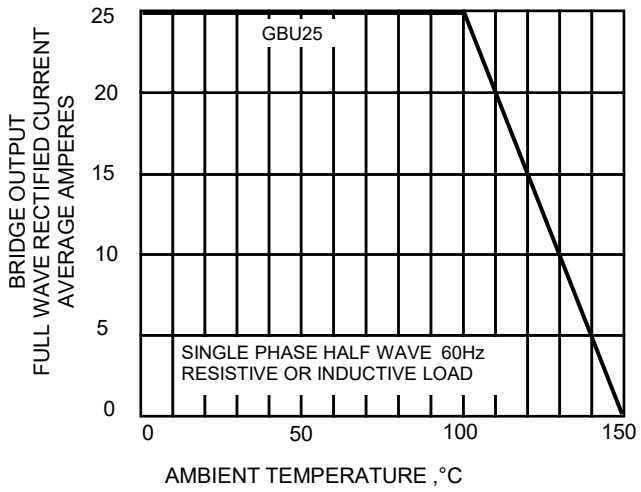


FIG.2-MAXIMUM NON-REPETITIVE SUNRGE CURRENT

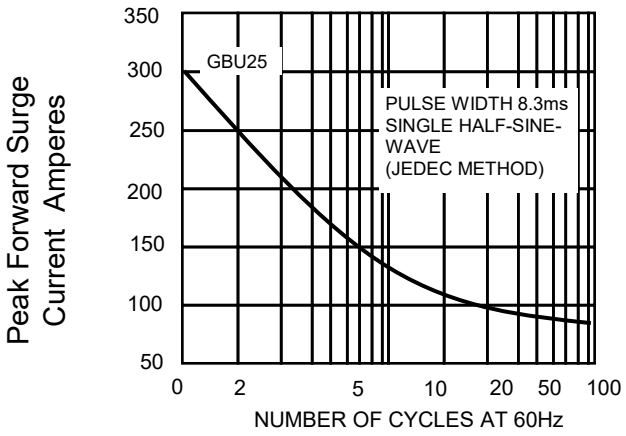


FIG.3-TYPICAL REVERSE CHARACTERISTICS

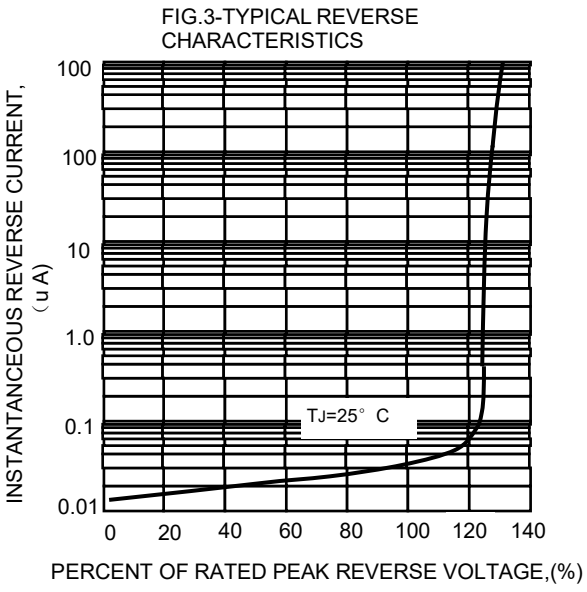
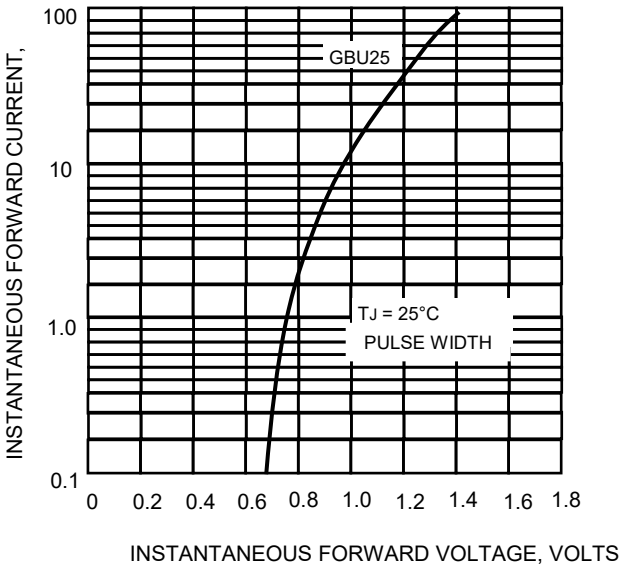
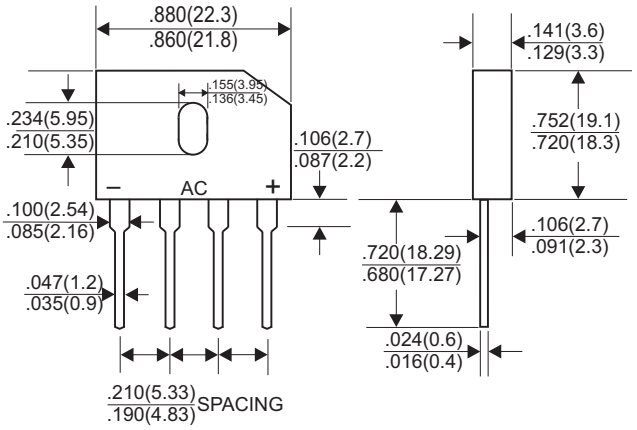


FIG.4-TYPICAL FORWARD CHARACTERISTICS



PACKAGE MECHANICAL DATA

GBU



Dimensions in inches and (millimeters)

REELSPECIFICATION

P/N	PKG	QTY
GBU25005-MS THRU GBU2510-MS	GBU	500

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